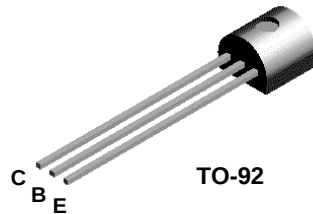
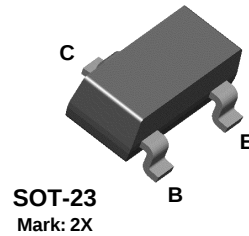


2N4401



MMBT4401



NPN General Purpose Amplifier

This device is designed for use as a medium power amplifier and switch requiring collector currents up to 500 mA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V_{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector Current - Continuous	600	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N4401	*MMBT4401	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

NPN General Purpose Amplifier

(continued)

2N4401 / MMBT4401

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 0.1 \text{ mA}, I_E = 0$	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 0.1 \text{ mA}, I_C = 0$	6.0		V
I_{BL}	Base Cutoff Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μA
I_{CEX}	Collector Cutoff Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μA

ON CHARACTERISTICS*

h_{FE}	DC Current Gain	$I_C = 0.1 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 150 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}$	20 40 80 100 40	300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.4 0.75	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	0.75	0.95 1.2	V V

SMALL SIGNAL CHARACTERISTICS

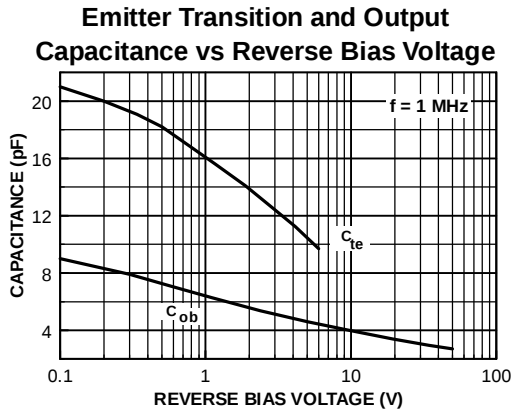
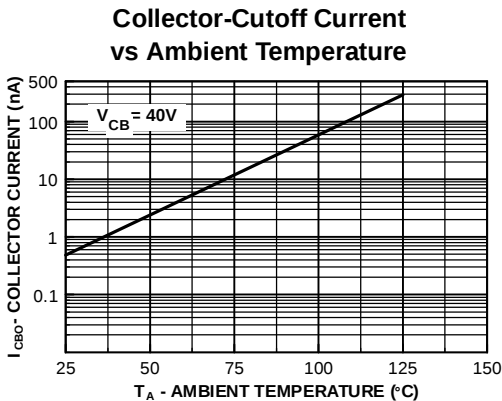
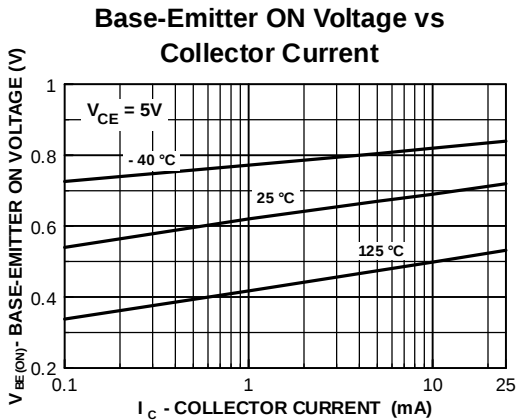
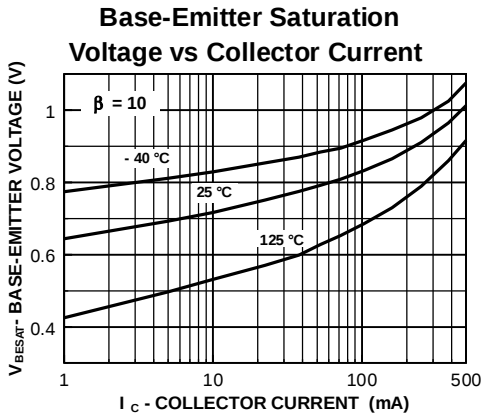
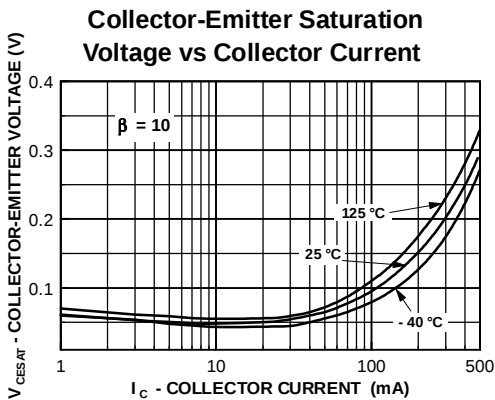
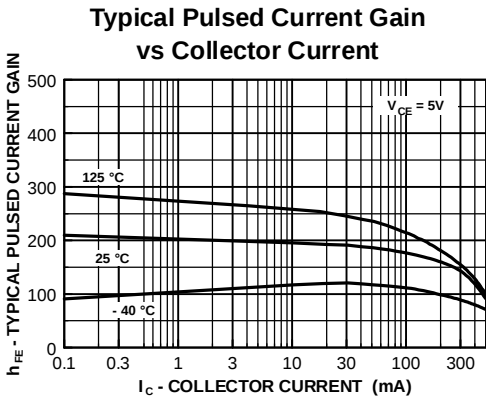
f_T	Current Gain - Bandwidth Product	$I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	250		MHz
C_{cb}	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0,$ $f = 140 \text{ kHz}$		6.5	pF
C_{eb}	Emitter-Base Capacitance	$V_{BE} = 0.5 \text{ V}, I_C = 0,$ $f = 140 \text{ kHz}$		30	pF
h_{ie}	Input Impedance	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$	1.0	15	k Ω
h_{re}	Voltage Feedback Ratio	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$	0.1	8.0	$\times 10^{-4}$
h_{fe}	Small-Signal Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$	40	500	
h_{oe}	Output Admittance	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$	1.0	30	μmhos

SWITCHING CHARACTERISTICS

t_d	Delay Time	$V_{CC} = 30 \text{ V}, V_{EB} = 2 \text{ V},$		15	ns
t_r	Rise Time	$I_C = 150 \text{ mA}, I_{B1} = 15 \text{ mA}$		20	ns
t_s	Storage Time	$V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}$		225	ns
t_f	Fall Time	$I_{B1} = I_{B2} = 15 \text{ mA}$		30	ns

*Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$

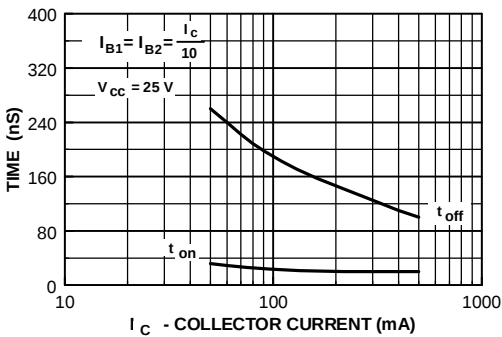
Typical Characteristics



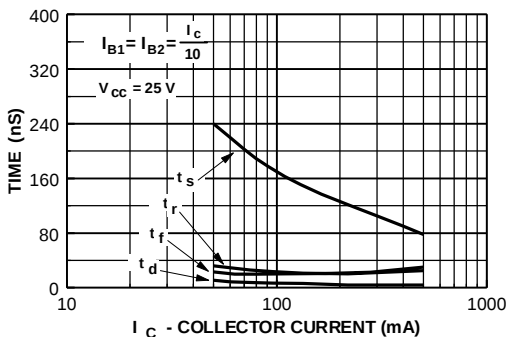
NPN General Purpose Amplifier
(continued)

Typical Characteristics (continued)

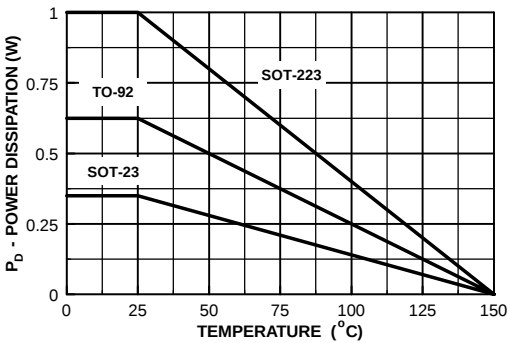
Turn On and Turn Off Times
vs Collector Current



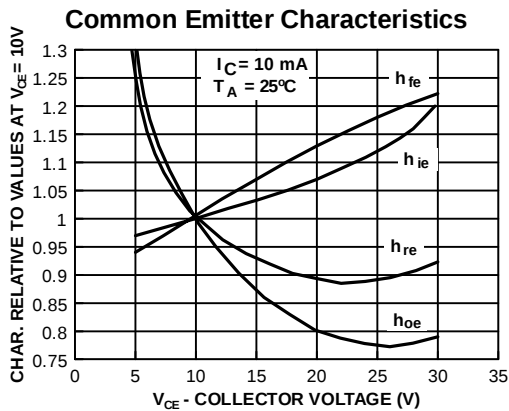
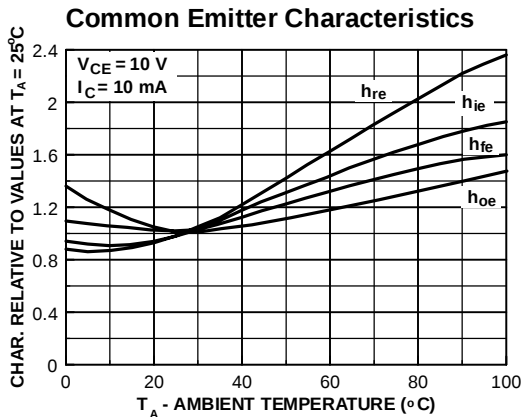
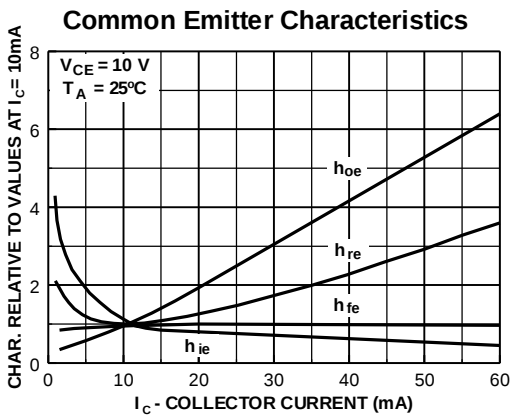
Switching Times
vs Collector Current



Power Dissipation vs
Ambient Temperature



Typical Common Emitter Characteristics (f = 1.0kHz)



Test Circuits

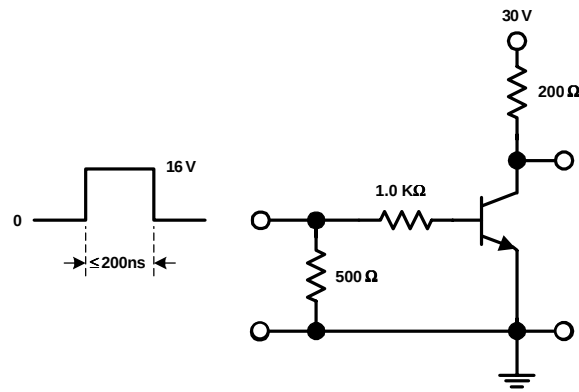


FIGURE 1: Saturated Turn-On Switching Timer

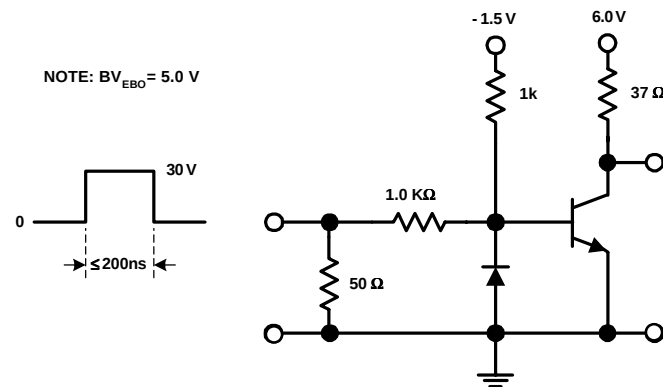


FIGURE 2: Saturated Turn-Off Switching Time

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